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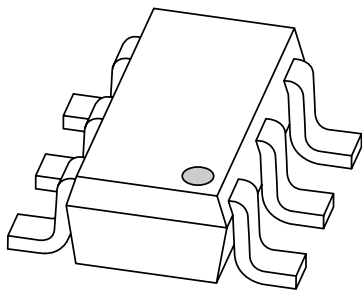
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Kind regards,

Team Nexperia

DATA SHEET



PBSS4350D

50 V low V_{CEsat} NPN transistor

Product data sheet
Supersedes data of 2001 Jan 26

2001 Jul 13

50 V low V_{CEsat} NPN transistor

PBSS4350D

FEATURES

- Low collector-emitter saturation voltage
- High current capability
- Improved device reliability due to reduced heat generation
- Replacement for SOT89/SOT223 standard packaged transistors due to enhanced performance.

APPLICATIONS

- Supply line switching circuits
- Battery management applications
- DC/DC convertor applications
- Strobe flash units
- Heavy duty battery powered equipment (motor and lamp drivers).

DESCRIPTION

NPN low V_{CEsat} transistor in a SOT457 (SC-74) plastic package. PNP complement: PBSS5350D.

MARKING

TYPE NUMBER	MARKING CODE
PBSS4350D	43

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	50	V
I_{CM}	peak collector current	5	A
R_{CEsat}	equivalent on-resistance	<145	m Ω

PINNING

PIN	DESCRIPTION
1	collector
2	collector
3	base
4	emitter
5	collector
6	collector

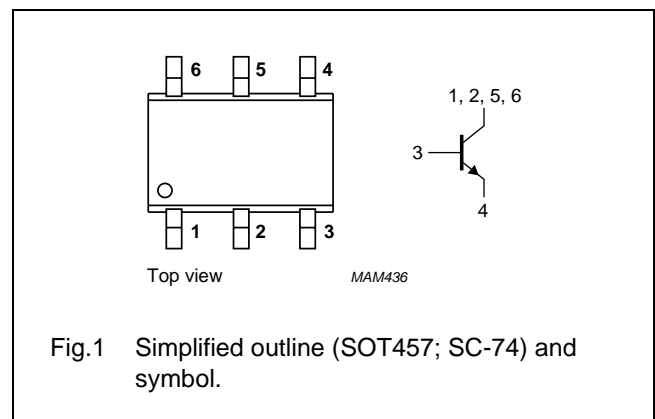


Fig.1 Simplified outline (SOT457; SC-74) and symbol.

50 V low V_{CEsat} NPN transistor

PBSS4350D

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	60	V
V_{CEO}	collector-emitter voltage	open base	–	50	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	3	A
I_{CM}	peak collector current		–	5	A
I_{BM}	peak base current		–	1	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	600	mW
		$T_{amb} \leq 25\text{ °C}$; note 2	–	750	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Notes

1. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm².
2. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 6 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	208	K/W
		in free air; note 2	160	K/W

Notes

1. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm².
2. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 6 cm².

50 V low V_{CEsat} NPN transistor

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CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

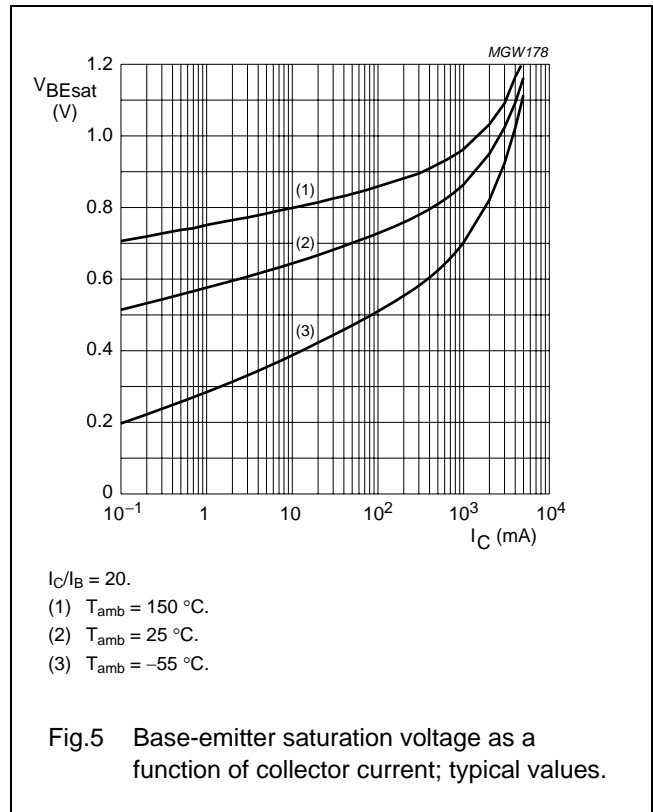
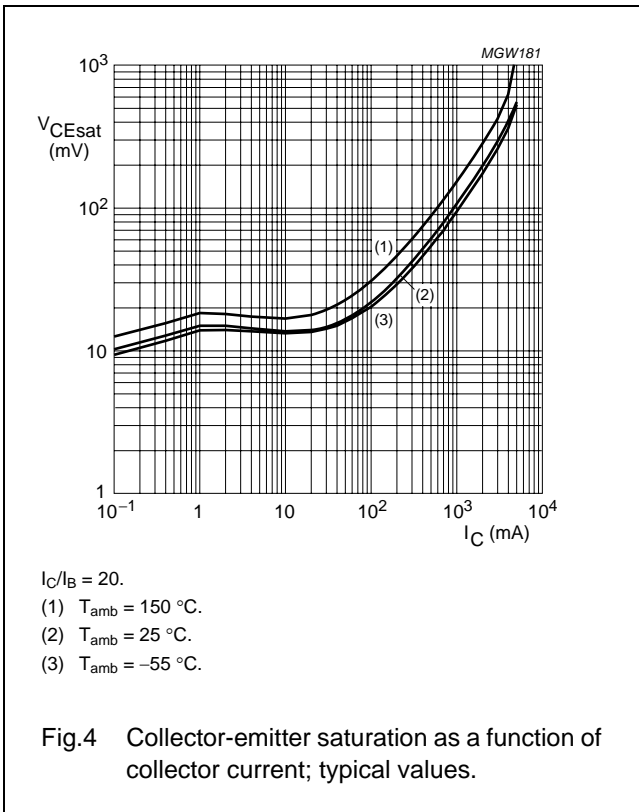
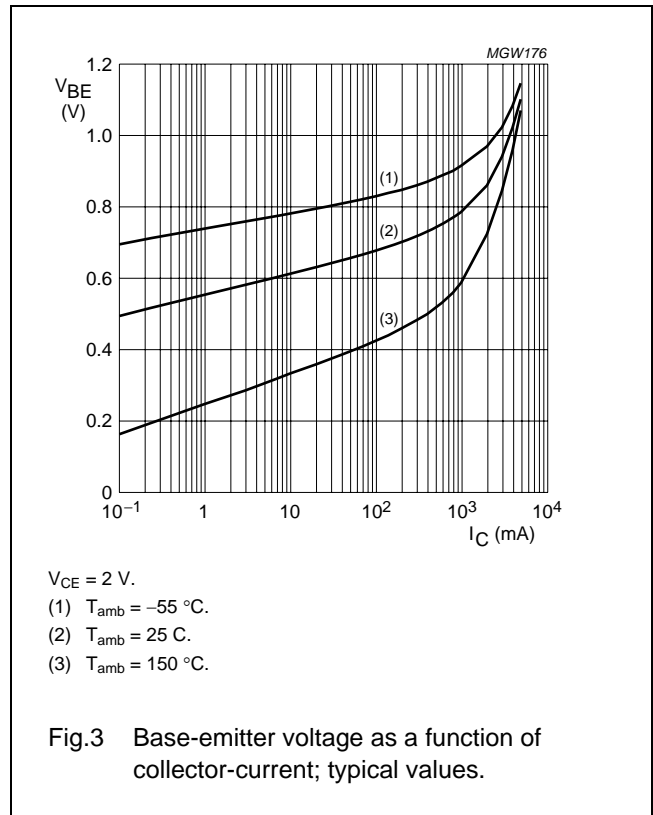
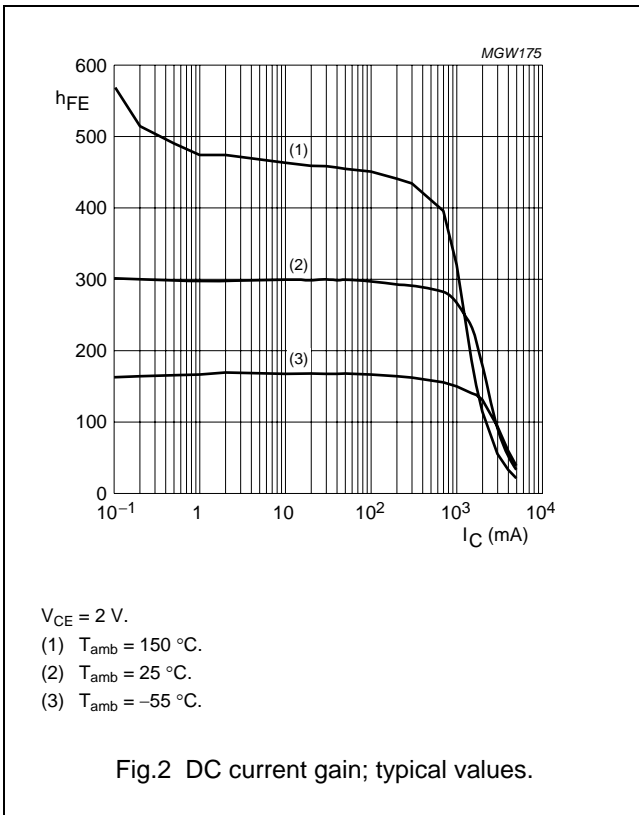
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = 50\text{ V}; I_E = 0$	–	–	100	nA
		$V_{CB} = 50\text{ V}; I_E = 0; T_j = 150\text{ °C}$	–	–	50	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0$	–	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 2\text{ V}; I_C = 500\text{ mA}$	200	–	–	
		$V_{CE} = 2\text{ V}; I_C = 1\text{ A}; \text{note 1}$	200	–	–	
		$V_{CE} = 2\text{ V}; I_C = 2\text{ A}; \text{note 1}$	100	–	–	
V_{CEsat}	collector -emitter saturation voltage	$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	–	90	mV
		$I_C = 1\text{ A}; I_B = 50\text{ mA}$	–	–	170	mV
		$I_C = 2\text{ A}; I_B = 200\text{ mA}; \text{note 1}$	–	–	290	mV
R_{CEsat}	equivalent on-resistance	$I_C = 2\text{ A}; I_B = 200\text{ mA}; \text{note 1}$	–	110	<145	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = 2\text{ A}; I_B = 200\text{ mA}; \text{note 1}$	–	–	1.2	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 1\text{ A}; \text{note 1}$	–	–	1.1	V
f_T	transition frequency	$I_C = 100\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
C_C	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$	–	–	30	pF

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

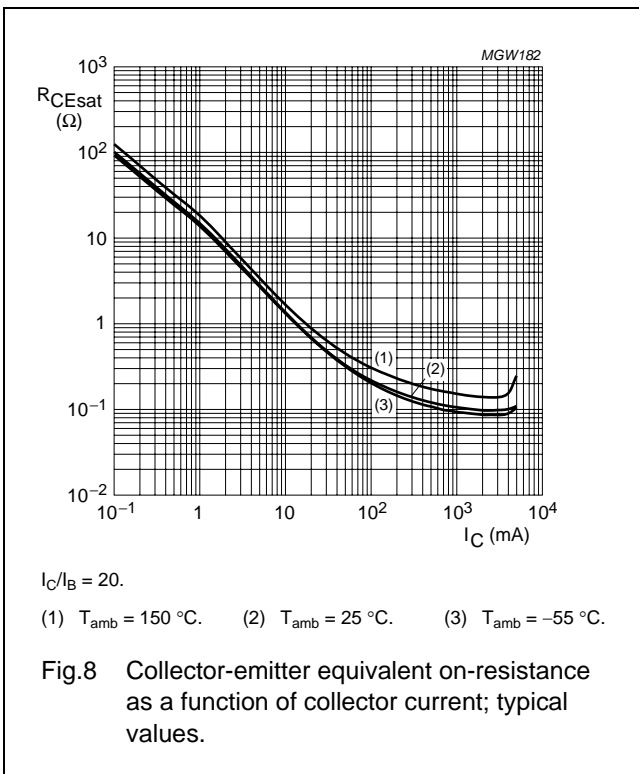
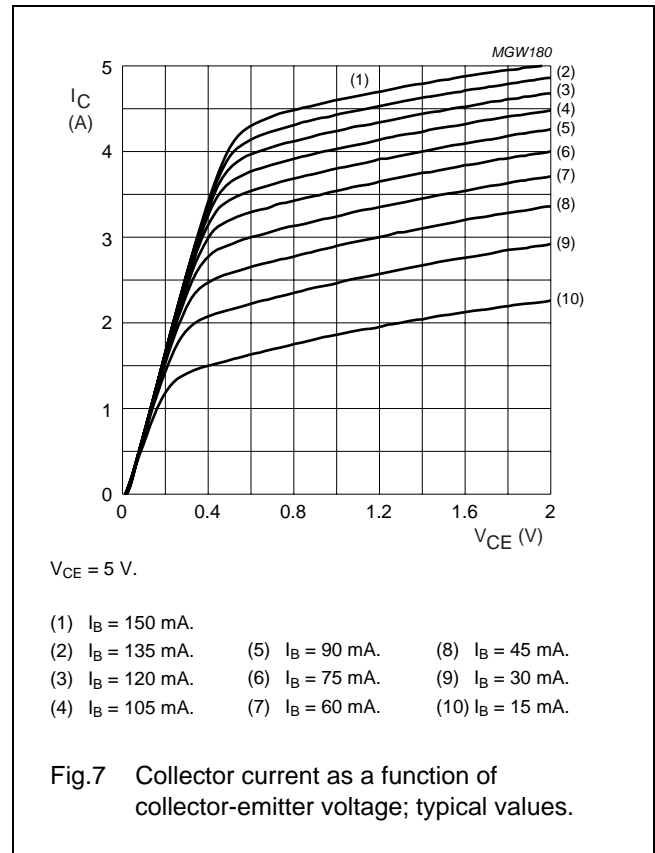
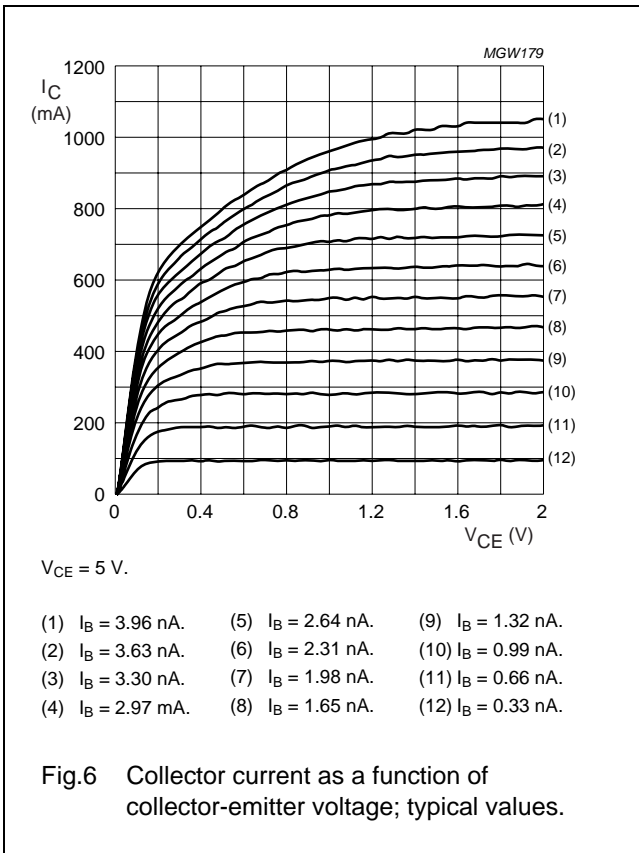
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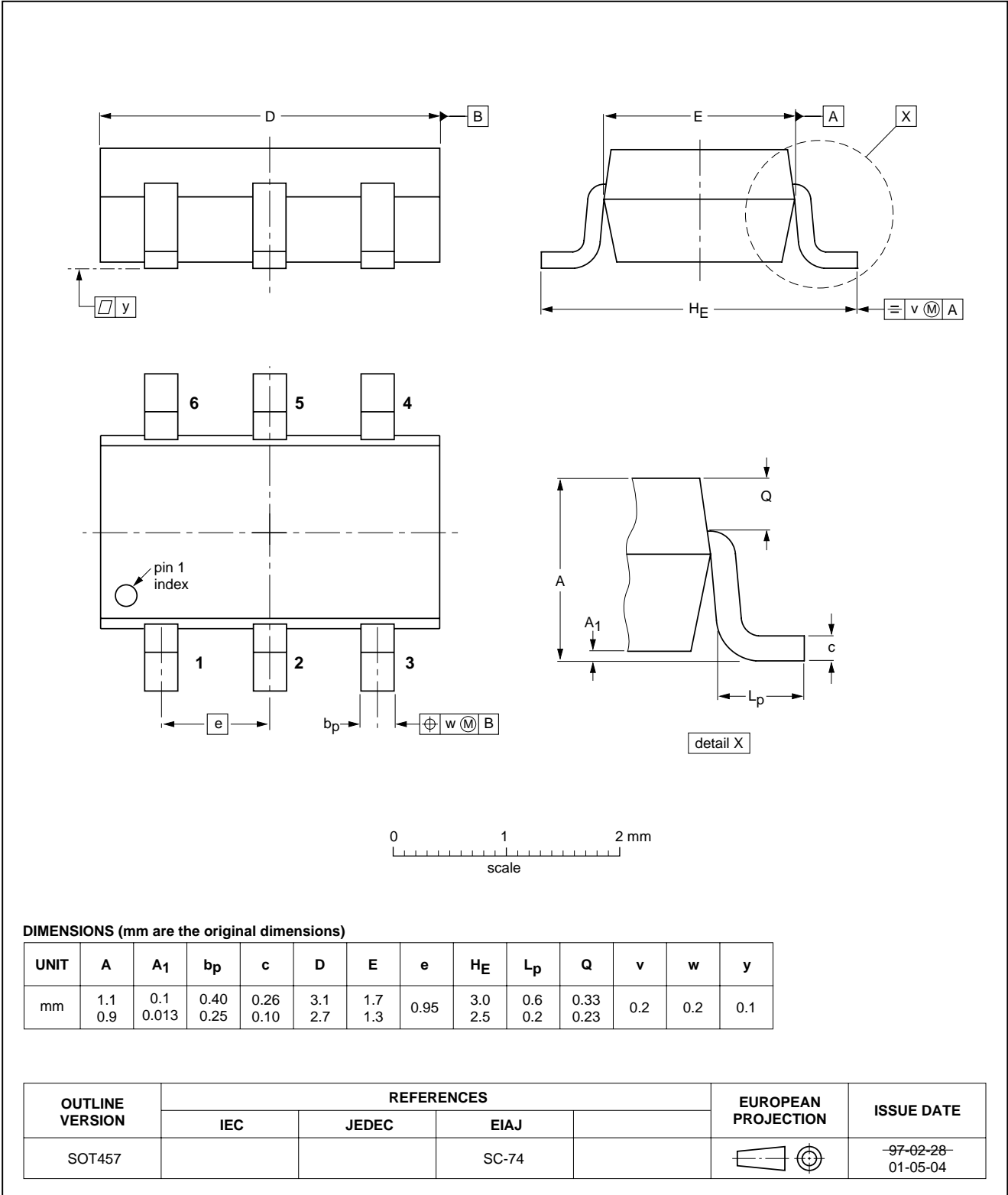
50 V low V_{CEsat} NPN transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT457



50 V low V_{CEsat} NPN transistor

PBSS4350D

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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